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S1	252	semiconductor with (fab fabricat\$4) with (simulat\$4 model\$4)	USPAT	OR	OFF	2005/07/20 13:11
S2	4	(fair adj model) or (fair adj diffusion adj model)	USPAT	OR	OFF	2005/07/20 13:11
S3	1	("6154717").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:24
S4	6	"10/989011" "10/780938" "10/668621" "09/891400" "09/781421" "09/519856"	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:29
S5	1428	703/2.ccls.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:29
S6	146	S5 and (diffusion impurit\$3 impure)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:31
S7	191	("pile-up" (pile adj up)) same (diffusion diffus\$4)	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/20 13:32
S8	1	10/059176	US-PGPUB	OR	OFF	2005/07/20 16:01
S10	1	"6581028".pn.	USPAT	OR	OFF	2005/07/20 17:15
S11	245	reverse adj short adj channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/07/20 17:15
S12	21	("5930494" "5819073" "5557710" "5684723" "6195790" "5148379" "6360190" "6242272" "6006026" "6080200" "5828586" "5889687" "6185472" "5819073" "6041424" "4584662" "6182270" "6011914" "6144932" "6360190" "6154717" "6505147" "6144929").pn.	USPAT	OR	OFF	2005/07/21 16:42

S13	13	("5103415" "5671395" "5675522" "5677846" "5774696" "5784302" "5819073" "5828586" "5889680" "5930494" "5963732" "6006026" "6011914").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/07/21 11:01
S14	19	(US-4607530-\$ or US-6594625-\$ or US-6006026-\$ or US-6684181-\$ or US-6327555-\$ or US-6285970-\$ or US-6154718-\$ or US-6154717-\$ or US-6148276-\$ or US-6144929-\$ or US-6120548-\$ or US-6041174-\$ or US-5999719-\$ or US-6581028-\$ or US-5557710-\$ or US-6242272-\$ or US-6505147-\$ or US-5889687-\$ or US-5930494-\$).did.	USPAT	OR	OFF	2005/07/21 11:53
S15	1	S14 and (SiO)	USPAT	OR	OFF	2005/07/21 11:53
S16	9	S14 and layer	USPAT	OR	OFF	2005/07/21 12:05
S17	5	S14 and (source drain)	USPAT	OR	OFF	2005/07/21 12:10
S18	4	S17 and distance	USPAT	OR	OFF	2005/07/21 13:17
S19	1	"6080200".pn.	USPAT	OR	OFF	2005/07/21 13:11
S20	258	(impurity adj diffusion) same (source drain) same (distance length)	USPAT	OR	OFF	2005/07/21 13:23
S21	39	S20 and (simulat\$4 model\$4)	USPAT	OR	OFF	2005/07/21 13:18



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 IEEE JNL IEEE Journal or Magazine
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☐ 1. Suppression of V_{th} fluctuation by minimizing transient enhanced diffusion in a quarter micron MOSFET
 Ono, A.; Sakai, I.;
 Electron Devices Meeting, 1996. International
 8-11 Dec. 1996 Page(s):755 - 758
 Digital Object Identifier 10.1109/EDM.1996.554090
 AbstractPlus | Full Text: EDE(208 KB) IEEE CNF

☐ 2. A detailed physical model for ion implant induced damage in silicon
 Tan, S.; Morris, M.F.; Morris, S.J.; Choudhury, B.; Geng Wang, Tash, A.F.; Si
 Electron Devices, IEEE Transactions on
 Volume 45, Issue 6, June 1998 Page(s):1228 - 1238
 Digital Object Identifier 10.1109/16.78523
 AbstractPlus | References | Full Text: EDE(308 KB) IEEE JNL

☐ 3. Systematic calibration for transient enhanced diffusion of indium and its
 0.15- μ m logic devices
 Jun-Ha Lee; Saung-Woo Lee; Jeong-Taek Kong; Young-Wing Kim;
 VLSI and CAD, 1999. ICVC 99, 8th International Conference on
 26-27 Oct. 1999 Page(s):53 - 56
 Digital Object Identifier 10.1109/ICVC.1999.820820
 AbstractPlus | Full Text: EDE(240 KB) IEEE CNF

☐ 4. Hydrogen in silicon: defect interactions and applications
 Ashok, S.;
 Solid-State and Integrated Circuit Technology, 1998. Proceedings, 1998 5th
 Conference on
 21-23 Oct. 1998 Page(s):749 - 752
 Digital Object Identifier 10.1109/ICSICT.1998.786120
 AbstractPlus | Full Text: EDE(212 KB) IEEE CNF

☐ 5. Modeling arsenic activation and diffusion during furnace and rapid therm
 Van den Bossche, E.; Jansen, H.; Garcia, B.;
 Electron Devices Meeting, 1995. International
 10-13 Dec. 1995 Page(s):81 - 84
 Digital Object Identifier 10.1109/EDM.1995.497187
 AbstractPlus | Full Text: EDE(256 KB) IEEE CNF

<http://ieeexplore.ieee.org/search/searchresult.jsp?query=&transient-enhanced+diffusion&s...> 7/21/2005

☐ 6. Multi-zone model for the transient enhanced diffusion of ion implanted in
 silicon during rapid thermal annealing
 Huang, T.H.; Kinoshita, H.; Kwong, D.L.;
 VLSI Technology, Systems, and Applications, 1993. Proceedings of Technical
 International Symposium on
 12-14 May 1993 Page(s):315 - 319
 Digital Object Identifier 10.1109/VLSA.1993.283670
 AbstractPlus | Full Text: EDE(280 KB) IEEE CNF

☐ 7. Explanation of reverse short channel effect by defect gradients
 Rattany, C.S.; Vuong, H.-H.; Estaghi, S.A.; Giles, M.D.; Panto, M.N.; Kilius
 Electron Devices Meeting, 1993. Technical Digest, International
 5-8 Dec. 1993 Page(s):311 - 314
 Digital Object Identifier 10.1109/EDM.1993.347345
 AbstractPlus | Full Text: EDE(256 KB) IEEE CNF

☐ 8. An anomalous crossover in V_{th} roll-off for indium-doped nMOSFETs
 Sun-Jay Chang; Chun-Yen Chang; Cuming Chen; Jih-Wen Chou; Tien-Sheng
 Huang;
 Electron Device Letters, IEEE
 Volume 21, Issue 8, Sept. 2000 Page(s):457 - 459
 Digital Object Identifier 10.1109/63.883110
 AbstractPlus | References | Full Text: EDE(62 KB) IEEE JNL

☐ 9. CV doping profiling of boron out-diffusion using an abrupt and highly dop
 buried epilayer
 Ortiz, C.J.; Naveer, L.K.; van Noort, W.D.; Scholtes, T.L.M.; Shuboom, J.W.;
 Microelectronic Test Structures, 2002. ICMTS 2002. Proceedings of the 2002 I
 Conference on
 8-11 April 2002 Page(s):83 - 88
 AbstractPlus | Full Text: EDE(475 KB) IEEE CNF

☐ 10. Suppression of lateral transient enhanced dopant diffusion by nitrogen li
 its application to fully depleted MOSFETs/SHOX
 Nakashima, S.; Takahashi, M.; Nakayama, S.; Ohno, T.;
 Ion Implantation Technology Proceedings, 1998 International Conference on
 Volume 1, 22-26 June 1998 Page(s):122 - 125 vol.1
 Digital Object Identifier 10.1109/IT.1998.812067
 AbstractPlus | Full Text: EDE(332 KB) IEEE CNF

☐ 11. High performance 0.18 μ m nMOSFET by TED suppression
 Hyun-Sik Kim; Jong-Hyon Ahn; Duk-Min Lee; So-Chul Lee; Kwang-Pyuk Su
 VLSI and CAD, 1999. ICVC 99, 8th International Conference on
 26-27 Oct. 1999 Page(s):140 - 142
 Digital Object Identifier 10.1109/ICVC.1999.820851
 AbstractPlus | Full Text: EDE(192 KB) IEEE CNF

☐ 12. A study of nonequilibrium diffusion modeling-applications to rapid therm
 and advanced bipolar technologies
 Bacca, B.; Wada, T.; Shigyo, N.; Norishima, M.; Nakajima, H.; Inou, K.; Iium
 Electron Devices, IEEE Transactions on
 Volume 39, Issue 3, March 1992 Page(s):348 - 361
 Digital Object Identifier 10.1109/16.123481
 AbstractPlus | Full Text: EDE(1380 KB) IEEE JNL

☐ 13. Effect of fluorine implantation dose on boron transient enhanced diffusio
 thermal diffusion in SiSub 1-xGeSub y
 Mubarek, H.A.W.E.; Kannurath, M.; Bonar, J.M.; Dillway, G.D.; Wang, Y.; H
 Willoughby, A.F.; Ashburn, P.;

<http://ieeexplore.ieee.org/search/searchresult.jsp?query=&transient-enhanced+diffusion&s...> 7/21/2005

- Electron Devices, IEEE Transactions on
Volume 52, Issue 4, Apr 2005 Page(s):519 - 526
Digital Object Identifier 10.1109/IED.2005.844738
AbstractPlus | References | Full Text: EDE(1208 KB) IEEE JNL
14. Grains-growth and clustering effects on boron diffusion in polysilicon during post-implantation annealing
Abadi, S.; Mansour, F.;
Microelectronics, 2004, ICM 2004 Proceedings: The 16th International Conference on
6-8 Dec. 2004 Page(s):475 - 479
Digital Object Identifier 10.1109/ICM.2004.1434702
AbstractPlus | Full Text: EDE(298 KB) IEEE CNF
15. Monte Carlo simulation of ion implantation (3-dimensional) and defect implantation process
Li, D.; Lin, L.; Wang, G.; Chen, Y.; Shrivastav, G.; Oak, S.; Tasch, A.F.; Baner, E.
Electron Devices Meeting, 2001. IEDM Technical Digest, International
2-5 Dec. 2001 Page(s):38.6.1 - 38.6.4
Digital Object Identifier 10.1109/IEDM.2001.979647
AbstractPlus | Full Text: EDE(320 KB) IEEE CNF
16. Modeling of arsenic transient enhanced diffusion and background boron low-energy As⁺ implanted Si
Ryungu Kim; Aoki, T.; Hirose, T.; Furuta, Y.; Hayashi, S.; Shano, T.; Taniguchi
Electron Devices Meeting, 2000. IEDM Technical Digest, International
10-13 Dec. 2000 Page(s):523 - 526
Digital Object Identifier 10.1109/IEDM.2000.904370
AbstractPlus | Full Text: EDE(300 KB) IEEE CNF
17. Novel aspects of the atomic transport of B implanted in silicon at energy
Pothier, V.; Napoléon, E.; Péro, F.; Morlet, S.; Rimpl, E.;
Ion Implantation Technology, 2000. Conference on
17-22 Sept. 2000 Page(s):163 - 168
Digital Object Identifier 10.1109/2000.924115
AbstractPlus | Full Text: EDE(344 KB) IEEE CNF
18. Modeling of boron deactivation/activation kinetics during ion implant and
Chakravathi, S.; Dunham, S.T.;
Simulation of Semiconductor Processes and Devices, 2000. SISPAD 2000. 20
Conference on
6-8 Sept. 2000 Page(s):167 - 170
Digital Object Identifier 10.1109/SISPAD.2000.871234
AbstractPlus | Full Text: EDE(212 KB) IEEE CNF
19. Novel species implantation using Applied Materials 9500uR™ and nR LE
Banks, P.; Dobson, M.; Kimbacher, B.; Allen, A.; Murrell, A.;
Ion Implantation Technology Proceedings, 1998 International Conference on
Volume 1, 22-26 June 1998 Page(s):358 - 361 vol.1
Digital Object Identifier 10.1109/IT.1998.812127
AbstractPlus | Full Text: EDE(232 KB) IEEE CNF
20. Evaluation of excess interstitial silicon amount using delta-doped boron
by UHV-CVD
Hiro, M.; Itozawa, T.; Hane, M.; Furukawa, A.;
Simulation of Semiconductor Processes and Devices, 1999. SISPAD 99. 1991
Conference on
6-8 Sept. 1999 Page(s):83 - 86
Digital Object Identifier 10.1109/SISPAD.1999.799260

- AbstractPlus | Full Text: EDE(248 KB) IEEE CNF
21. Boron diffusion in ultra low-energy (<1 keV/ion) deuterium (D⁰ or D¹⁺)
Kusaba, T.; Shimada, N.; Aoki, T.; Matsuo, J.; Yamada, I.; Goto, K.; Sugii, T.;
Ion Implantation Technology Proceedings, 1998 International Conference on
Volume 2, 22-26 June 1998 Page(s):126 - 1281 vol.2
Digital Object Identifier 10.1109/IT.1998.813920
AbstractPlus | Full Text: EDE(378 KB) IEEE CNF
22. Fluorine effect on boron diffusion: chemical or damage?
Liu, J.; Downey, D.F.; Jones, K.S.; Ishida, E.;
Ion Implantation Technology Proceedings, 1998 International Conference on
Volume 2, 22-26 June 1998 Page(s):351 - 354 vol.2
Digital Object Identifier 10.1109/IT.1998.813335
AbstractPlus | Full Text: EDE(284 KB) IEEE CNF
23. A novel unified transient enhanced diffusion model on the basis of RSF v
database
Sato, H.; Tsuneno, K.; Masuda, H.;
Microelectronic Test Structures, 1998. ICMTS 1998, Proceedings of the 1998
Conference on
23-26 March 1998 Page(s):193 - 196
Digital Object Identifier 10.1109/ICMITS.1998.689067
AbstractPlus | Full Text: EDE(216 KB) IEEE CNF
24. A physics-based modeling approach for the simulation of anomalous boron
clustering behaviors
Lluch, A.D.; Enríes, S.K.; Jones, K.S.; Law, M.E.; Giles, M.D.;
Electron Devices Meeting, 1997. Technical Digest, International
7-10 Dec. 1997 Page(s):493 - 496
Digital Object Identifier 10.1109/IEDM.1997.650431
AbstractPlus | Full Text: EDE(308 KB) IEEE CNF
25. Ion implantation and transient enhanced diffusion
Pothier, V.M.; Eaglesham, D.J.; Gilmer, G.H.; Gossmann, H.-J.; Janitz, M.; Raulo
P.A.;
Electron Devices Meeting, 1995. International
10-13 Dec. 1995 Page(s):77 - 80
Digital Object Identifier 10.1109/IEDM.1995.497188
AbstractPlus | Full Text: EDE(352 KB) IEEE CNF

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1. Two-dimensional simulation for resonant tunneling transistor
 Tomizawa, M.; Tanigawa, H.; Yoshii, A.;
 Electron Devices, IEEE Transactions on
 Volume 41, Issue 6, June 1994 Page(s):883 - 887
 Digital Object Identifier 10.1109/16.283297
 AbstractPlus | Full Text: EDE(948 KB) IEEE JNL

2. Studies of solid liner stability in electromagnetic implications
 Aitchison, W.L.; Faehl, R.J.; Raimore, R.E.; Morgan, D.;
 Plasma Science, 1989, 25th Anniversary, IEEE Conference Record - Abstracts
 International on
 1-4 June 1988 Page(s):246
 Digital Object Identifier 10.1109/PLASMA.1988.677792
 AbstractPlus | Full Text: EDE(98 KB) IEEE CNF

3. Two dimensional simulation of transient enhanced boron out-diffusion in
 SiGe HBT due to an extrinsic base implant
 Hashin, M.D.R.; Lever, R.F.; Ashburn, P.;
 Bipolar/BICMOS Circuits and Technology Meeting, 1997. Proceedings of the
 28-30 Sept. 1997 Page(s):96 - 99
 Digital Object Identifier 10.1109/BIPOL.1997.647365
 AbstractPlus | Full Text: EDE(349 KB) IEEE CNF

4. Effects of wall ablation on the internal structure and dynamics of a ring
 Fries, M.H.;
 Plasma Science, 1989, IEEE Conference Record - Abstracts, 1989 IEEE Inter
 Conference on
 22-24 May 1989 Page(s):37 - 38
 Digital Object Identifier 10.1109/PLASMA.1989.165962
 AbstractPlus | Full Text: EDE(152 KB) IEEE CNF

5. Two dimensional numerical simulation of submicron GaAs MESFETs
 Sang Hee Son, Kae Dal Kweck,
 Electronic Manufacturing Technology Symposium, 1989, Proceedings, Japan I
 Sixt IEEE/CHMT International
 26-28 April 1989 Page(s):234 - 237
 Digital Object Identifier 10.1109/EMTS.1989.78145
 AbstractPlus | Full Text: EDE(328 KB) IEEE CNF

6. Two-Dimensional Numerical Simulation of Impurity Redistribution in VLS
 Tzient, R.;
 Solid-State Circuits, IEEE Journal of
 Volume 15, Issue 4, Aug 1980 Page(s):544 - 548
 AbstractPlus | Full Text: EDE(632 KB) IEEE JNL

7. Two-dimensional process simulation using verified phenomenological m
 Fair, R.B.; Gardner, C.L.; Johnson, M.J.; Kenkel, S.W.; Rose, D.J.; Rose, J.E.;
 R.;
 Computer-Aided Design of Integrated Circuits and Systems, IEEE Transac
 Volume 10, Issue 5, May 1991 Page(s):943 - 951
 Digital Object Identifier 10.1109/43.78501
 AbstractPlus | Full Text: EDE(688 KB) IEEE JNL

8. An improved two-dimensional simulation model (MEGA) for GaAs MESFE
 LSI design
 Hirose, M.; Yoshida, J.; Toyoda, N.;
 Computer-Aided Design of Integrated Circuits and Systems, IEEE Transac
 Volume 7, Issue 2, Feb. 1988 Page(s):225 - 230
 Digital Object Identifier 10.1109/43.3152
 AbstractPlus | Full Text: EDE(664 KB) IEEE JNL

9. Two-dimensional simulation of laser diodes in the steady state
 Kapon, K.B.;
 Quantum Electronics, IEEE Journal of
 Volume 24, Issue 4, April 1988 Page(s):641 - 651
 Digital Object Identifier 10.1109/3.173
 AbstractPlus | Full Text: EDE(672 KB) IEEE JNL

10. Two-dimensional numerical simulation of Fermi-level pinning phenome
 centers in AlGaAs/GaAs HEMTs
 Mizuta, H.; Yamaguchi, K.; Yamane, M.; Tanoue, T.; Takahashi, S.;
 Electron Devices, IEEE Transactions on
 Volume 36, Issue 10, Oct. 1989 Page(s):2307 - 2314
 Digital Object Identifier 10.1109/16.40915
 AbstractPlus | Full Text: EDE(664 KB) IEEE JNL

11. Numerical simulation and comparison of Si BJTs and Si_{1-x}Ge_x HBTs
 Pejcharov, B.; Kay, L.E.; Tang, T.-W.; Navon, D.H.;
 Electron Devices, IEEE Transactions on
 Volume 36, Issue 10, Oct. 1989 Page(s):2129 - 2137
 Digital Object Identifier 10.1109/16.40892
 AbstractPlus | Full Text: EDE(760 KB) IEEE JNL

12. Simulation of a GaAs MESFET including velocity overshoot: an extended
 formalism
 Kizlyail, I.C.; Anali, M.;
 Electron Device Letters, IEEE
 Volume 10, Issue 9, Sept. 1989 Page(s):405 - 408
 Digital Object Identifier 10.1109/55.34724
 AbstractPlus | Full Text: EDE(664 KB) IEEE JNL

13. Trends in diffusion-length measurements in the original and dielectricall
 silicon as a function of processing
 Burk, D.E.; Chung, B.C.;
 Electron Devices, IEEE Transactions on
 Volume 36, Issue 4, Part 2, April 1989 Page(s):750 - 760

- Digital Object Identifier 10.1109/16.22481
AbstractPlus | Full Text: PDF(676 KB) IEEE JNL
14. A new approach to the simulation of the coupled point defects and Impu
Rortis, E.; O'Brien, R.R.; Morehead, F.F.; Lower, R.F.; Peng, J.P.; Srinivasan,
Computer-Aided Design of Integrated Circuits and Systems, IEEE Transaction
Volume 8, Issue 10, Oct. 1990 Page(s):1113 - 1122
Digital Object Identifier 10.1109/43.52735
AbstractPlus | Full Text: PDF(628 KB) IEEE JNL
15. The new two-dimensional electron gas base HBT (2DEG-HBT): two-dimen
numerical simulation
Rabinzohn, P.D.; Usagawa, T.; Mizuta, H.; Yamaguchi, K.;
Electron Devices, IEEE Transactions on
Volume 38, Issue 2, Feb. 1991 Page(s):222 - 231
Digital Object Identifier 10.1109/16.69898
AbstractPlus | Full Text: PDF(648 KB) IEEE JNL
16. Overgrown silicon PBTs: calculations and measurements
Schuppen, A.; Marso, M.; Lunz, H.;
Electron Devices, IEEE Transactions on
Volume 41, Issue 5, May 1994 Page(s):751 - 760
Digital Object Identifier 10.1109/16.285028
AbstractPlus | Full Text: PDF(656 KB) IEEE JNL
17. An advanced model for dopant diffusion in polysilicon
Puchner, H.; Seibehner, S.;
Electron Devices, IEEE Transactions on
Volume 42, Issue 10, Oct 1995 Page(s):1750 - 1755
Digital Object Identifier 10.1109/16.464423
AbstractPlus | Full Text: PDF(468 KB) IEEE JNL
18. THASIM: compact and efficient two-dimensional transient simulator for a
semiconductor devices
Ohracht, M.S.; Elmasy, M.I.; Heasol, E.L.;
Computer-Aided Design of Integrated Circuits and Systems, IEEE Transaction
Volume 14, Issue 4, April 1995 Page(s):447 - 458
Digital Object Identifier 10.1109/43.372371
AbstractPlus | Full Text: PDF(680 KB) IEEE JNL
19. Two-dimensional modeling of the enhanced diffusion in thin base n-p-n
transistors after lateral ion implantations
Denorme, S.; Mathet, D.; Dolfus, P.; Meula, M.;
Electron Devices, IEEE Transactions on
Volume 42, Issue 3, March 1995 Page(s):523 - 527
Digital Object Identifier 10.1109/16.368049
AbstractPlus | Full Text: PDF(636 KB) IEEE JNL
20. Analysis and optimization of InGaAsP electro-absorption modulators
Meglio, D.; Lugli, P.; Sabella, R.; Sahlen, O.;
Quantum Electronics, IEEE Journal of
Volume 31, Issue 2, Feb. 1995 Page(s):261 - 268
Digital Object Identifier 10.1109/3.348054
AbstractPlus | Full Text: PDF(658 KB) IEEE JNL
21. Quasi-three-dimensional modeling of sub-micron LOCOS structures
Park, H.; Smeys, P.; Sahul, Z.H.; Saraswat, K.C.; Dutton, R.W.; Hojung Hweon
Semiconductor Manufacturing, IEEE Transactions on

- Volume 8, Issue 4, Nov. 1995 Page(s):390 - 401
Digital Object Identifier 10.1109/66.475180
AbstractPlus | Full Text: PDF(1012 KB) IEEE JNL
22. A two-dimensional multispecies fluid model of the plasma in an AC plas
Campbell, R.B.; Veenasingam, R.; McGrath, R.T.;
Plasma Science, IEEE Transactions on
Volume 23, Issue 4, Aug. 1995 Page(s):698 - 708
Digital Object Identifier 10.1109/27.467992
AbstractPlus | Full Text: PDF(1076 KB) IEEE JNL
23. Grid adaption near moving boundaries in two dimensions for IC process
Law, M.E.;
Computer-Aided Design of Integrated Circuits and Systems, IEEE Transaction
Volume 14, Issue 10, Oct. 1995 Page(s):1223 - 1230
Digital Object Identifier 10.1109/43.468338
AbstractPlus | Full Text: PDF(680 KB) IEEE JNL
24. Discretization of flux densities in device simulations using optimum anti
Ting-Ywei Tong; Melkci leong;
Computer-Aided Design of Integrated Circuits and Systems, IEEE Transaction
Volume 14, Issue 11, Nov. 1995 Page(s):1309 - 1315
Digital Object Identifier 10.1109/43.468658
AbstractPlus | Full Text: PDF(488 KB) IEEE JNL
25. DBL considerations of extended drain structure for 0.1 μ m MOSFETs
Jiunn-Yann Tsai; Jia Sun; Yea, K.F.; Osburn, C.M.;
Electron Device Letters, IEEE
Volume 17, Issue 7, July 1996 Page(s):331 - 333
Digital Object Identifier 10.1109/55.506358
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1. On Identification of certain nonlinear systems (Corresp.)

Hayashi, H.;

Information Theory, IEEE Transactions on
Volume 18, Issue 6, Nov 1972 Page(s):809 - 811

AbstractPlus | Full Text: EDE(392 KB) IEEE JNL

2. Temperature dependence of threshold current in GaAs double-hetero-

with emission wavelengths of 0.74-0.8um

Hayakawa, T.; Yamamoto, S.; Hayashi, H.; Sakurai, T.; Hijikata, T.;

Quantum Electronics, IEEE Journal of
Volume 17, Issue 11, Nov 1981 Page(s):2205 - 2210

AbstractPlus | Full Text: EDE(1920 KB) IEEE JNL

3. Mode characteristics of large-optical-cavity V-channelled substrate inner-

lasers

Hayakawa, T.; Suyama, T.; Hayashi, H.; Yamamoto, S.; Yano, S.; Hijikata, T.;

Quantum Electronics, IEEE Journal of
Volume 19, Issue 10, Oct 1983 Page(s):1530 - 1536

AbstractPlus | Full Text: EDE(858 KB) IEEE JNL

4. 680 nm CW operation at room temperature by AlGaAs double heterojunc-

Quantum Electronics, IEEE Journal of
Volume 19, Issue 6, Jun 1983 Page(s):1009 - 1015

AbstractPlus | Full Text: EDE(908 KB) IEEE JNL

5. Programmable optical guided-wave device using Bi12SiO20 crystals

Hayashi, H.; Fujii, Y.;

Quantum Electronics, IEEE Journal of
Volume 14, Issue 11, Nov 1978 Page(s):848 - 854

AbstractPlus | Full Text: EDE(744 KB) IEEE JNL

6. High picture quality TV receiver with IDTV system

Sunada, K.; Sato, H.; Fujita, S.; Kawasaka, E.; Nishida, M.; Okada, Y.;

Consumer Electronics, IEEE Transactions on
Volume 34, Issue 4, Nov. 1988 Page(s):856 - 865

Digital Object Identifier 10.1109/30.8895

http://ieeexplore.ieee.org/search/searchresult.jsp?disp=cit&queryText=(Hayashi%20H.<in>... 7/21/2005

AbstractPlus | Full Text: EDE(1028 KB) IEEE JNL

7. Substrate effects on the magnetic characteristics of sputtered media

Onishi, Y.; Matsumura, H.; Hase, T.;

Magnetics, IEEE Transactions on
Volume 25, Issue 5, Sep 1988 Page(s):3887 - 3889

Digital Object Identifier 10.1109/20.42468

AbstractPlus | Full Text: EDE(488 KB) IEEE JNL

8. Effect of polar groups on the electrical breakdown strength of plasma-po-

Nakano, T.; Fukuyama, M.; Hayashi, H.; Ishi, K.; Ono, Y.;

Electrical Insulation, IEEE Transactions on (see also Dielectrics and Electrical
Transactions on)
Volume 25, Issue 6, Dec. 1990 Page(s):1085 - 1091

Digital Object Identifier 10.1109/14.84493

AbstractPlus | Full Text: EDE(392 KB) IEEE JNL

9. Low-noise current optoelectronic integrated receiver with internal equal-

per-second long-wavelength optical communications

Yano, H.; Aga, K.; Kamel, H.; Saeki, G.; Hayashi, H.;

Optics Technology, Journal of
Volume 8, Issue 9, Sep 1990 Page(s):1328 - 1333

Digital Object Identifier 10.1109/50.59161

AbstractPlus | Full Text: EDE(532 KB) IEEE JNL

10. Mass production back-grinding/water-thinning technology for GaAs devi-

Nishijuchi, M.; Goto, N.; Sakiguchi, T.; Nishizawa, H.; Hayashi, H.; Ono, K.;

Components, Hybrids, and Manufacturing Technology, IEEE Transactions on
Trans. on Components, Packaging, and Manufacturing Technology, Part A, B,
Volume 13, Issue 3, Sept. 1990 Page(s):528 - 533

Digital Object Identifier 10.1109/33.58855

AbstractPlus | Full Text: EDE(524 KB) IEEE JNL

11. A novel self-aligned gate process for half-micrometer gate GaAs ICs usin-

Shikida, S.; Tsuchimoto, J.; Hayashi, H.;

Electron Devices, IEEE Transactions on
Volume 37, Issue 6, Aug. 1990 Page(s):1800 - 1803

Digital Object Identifier 10.1109/16.57129

AbstractPlus | Full Text: EDE(460 KB) IEEE JNL

12. Radiation tolerant GaAs MESFET with a highly-doped thin active layer gr-

Nishijuchi, M.; Hashigata, T.; Nishizawa, H.; Hayashi, H.; Okazaki, N.; Kikaga

Nuclear Science, IEEE Transactions on
Volume 37, Issue 6, Part 2, Dec. 1990 Page(s):2071 - 2075

Digital Object Identifier 10.1109/23.101231

AbstractPlus | Full Text: EDE(384 KB) IEEE JNL

13. A highly efficient adaptive mesh approach to semiconductor device simu-

application to impact ionization analysis

Dang, R.; Matsushita, K.;

Magnetics, IEEE Transactions on
Volume 27, Issue 5, Sep 1991 Page(s):4182 - 4185

Digital Object Identifier 10.1109/20.105018

AbstractPlus | Full Text: EDE(300 KB) IEEE JNL

14. X-band MMIC amplifier with pulse-doped GaAs MESFETs

Nishijuchi, M.; Nakajima, S.; Otsu, K.;

Sakiguchi, T.; Kuwata, N.; Matsuzaki, K.;

Microwave Theory and Techniques, IEEE Transactions on

http://ieeexplore.ieee.org/search/searchresult.jsp?disp=cit&queryText=(Hayashi%20H.<in>... 7/21/2005

- Volume 39, Issue 12, Dec 1991 Page(s):1987 - 1994
Digital Object Identifier 10.1109/22.106537
AbstractPlus | Full Text: PDE(792 KB) IEEE JNL
15. A high-speed eight-channel optoelectronic integrated receiver array com-
p-4-n PD's and AlInGa/GaInAs HEMTs
Yano, H.; Murata, M.; Sasaki, G.; Hayashi, H.;
Uphwave Technology, Journal of
Volume 10, Issue 7, July 1992 Page(s):833 - 837
Digital Object Identifier 10.1109/50.144916
AbstractPlus | Full Text: PDE(460 KB) IEEE JNL
16. A multichip packaged GaAs 16x16 parallel multiplier
Sakaguchi, T.; Sawada, S.; Hirose, T.; Nishiguchi, M.; Shiga, N.; Hayashi, H.;
Components, Hybrids, and Manufacturing Technology, IEEE Transactions on
Trans. on Components, Packaging, and Manufacturing Technology, Part A, B,
Volume 15, Issue 4, Aug. 1992 Page(s):444 - 450
Digital Object Identifier 10.1109/93.159872
AbstractPlus | Full Text: PDE(672 KB) IEEE JNL
17. An ultra-high-speed optoelectronic integrated receiver for fiber-optic com-
Yano, H.; Sasaki, G.; Murata, M.; Hayashi, H.;
Electron Devices, IEEE Transactions on
Volume 39, Issue 10, Oct. 1992 Page(s):2254 - 2259
Digital Object Identifier 10.1109/16.158796
AbstractPlus | Full Text: PDE(652 KB) IEEE JNL
18. MMIC family for DBS down-converter with pulse-doped GaAs MESFETs
Shiga, N.; Sakaguchi, T.; Nakajima, S.; Otsubo, K.; Kuwata, N.; Matsuzaki, K.;
Solid-State Circuits, IEEE Journal of
Volume 27, Issue 10, Oct. 1992 Page(s):1413 - 1420
Digital Object Identifier 10.1109/4.156445
AbstractPlus | Full Text: PDE(1016 KB) IEEE JNL
19. Low-noise characteristics of pulse-doped GaAs MESFETs with planar ge-
Nakajima, S.; Otsubo, K.; Shiga, N.; Kuwata, N.; Matsuzaki, K.; Sakaguchi, T.;
Electron Devices, IEEE Transactions on
Volume 39, Issue 4, April 1992 Page(s):771 - 776
Digital Object Identifier 10.1109/16.127464
AbstractPlus | Full Text: PDE(652 KB) IEEE JNL
20. Intelligent manufacturing
Hayashi, H.;
Spectrum, IEEE
Volume 30, Issue 8, Sept. 1993 Page(s):82 - 84
Digital Object Identifier 10.1109/6.275168
AbstractPlus | Full Text: PDE(424 KB) IEEE JNL
21. A non-isothermal device simulator for MOSFET analysis
Hayashi, H.; Dang, R.;
Magnetics, IEEE Transactions on
Volume 29, Issue 2, Mar 1993 Page(s):2047 - 2050
Digital Object Identifier 10.1109/20.250813
AbstractPlus | Full Text: PDE(312 KB) IEEE JNL
22. Nondestructive readout mode static induction transistor (SIT) photo semi-
Nakamura, J.; Gomi, Y.; Uchi, M.; Hayashi, H.;
Electron Devices, IEEE Transactions on

[http://ieeexplore.ieee.org/search/searchresult.jsp?d=sp=ci&queryText=\(hayashi%20h.<in>...](http://ieeexplore.ieee.org/search/searchresult.jsp?d=sp=ci&queryText=(hayashi%20h.<in>...) 7/21/2005

- Volume 40, Issue 2, Feb. 1993 Page(s):334 - 341
Digital Object Identifier 10.1109/16.182510
AbstractPlus | Full Text: PDE(712 KB) IEEE JNL
23. Strain-induced effects on the performance of AlGaInP visible lasers
Hashimoto, J.; Katsuyama, T.; Yoshida, I.; Hayashi, H.;
Quantum Electronics, IEEE Journal of
Volume 29, Issue 6, June 1993 Page(s):1693 - 1698
Digital Object Identifier 10.1109/93.234445
AbstractPlus | Full Text: PDE(640 KB) IEEE JNL
24. Characterization of double pulse-doped channel GaAs MESFETs
Nakajima, S.; Kuwata, N.; Shiga, N.; Otsubo, K.; Matsuzaki, K.; Sakaguchi, T.;
Electron Device Letters, IEEE
Volume 14, Issue 3, March 1993 Page(s):146 - 148
Digital Object Identifier 10.1109/65.215139
AbstractPlus | Full Text: PDE(204 KB) IEEE JNL
25. Present status of design and manufacture of the superconducting magni-
Helical Device
Saitow, T.; Yamamoto, J.; Takahata, K.; Imagawa, S.; Tamura, H.; Yano, N.;
Nishimura, A.; Satoh, S.; Yamazaki, K.; Kaneko, H.; Yonezu, H.; Hayashi, H.;
Matsuzaki, O.;
Applied Superconductivity, IEEE Transactions on
Volume 3, Issue 1, Part 4, Mar 1993 Page(s):365 - 368
Digital Object Identifier 10.1109/77.233469
AbstractPlus | Full Text: PDE(388 KB) IEEE JNL

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[http://ieeexplore.ieee.org/search/searchresult.jsp?d=sp=ci&queryText=\(hayashi%20h.<in>...](http://ieeexplore.ieee.org/search/searchresult.jsp?d=sp=ci&queryText=(hayashi%20h.<in>...) 7/21/2005

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Monte Carlo simulation of impurity diffusion in thin-film ...

Title: Monte Carlo simulation of impurity diffusion in thin-film diffusion barriers
Authors: Lavine, JP Journal: Journal of Applied Physics, Volume 59, ...

http://www.google.com/search?hl=en&q=impurity+diffusion+simulation

7/21/2005

adsabs.harvard.edu/abs/1986JAP....59.1986L - Similar pages

Taurus Process Atomistic - Data sheet

Taurus Process Atomistic provides fast and accurate diffusion simulation ...
With each technology node, the number of impurity atoms per transistor is ...
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The Efficient Simulation of Coupled Point Defect and Impurity Diffusion by an Adaptive Mulligrnd Method D. Pantic, S. Milajkovic, S. Mitrovic and N. ...
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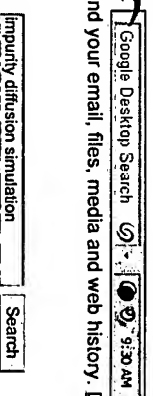
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7/21/2005


14. New analytic models and efficient parameter extraction for computational and 2-D ion implantation modeling
Balasubramanian, G.; Obradovic, B.; Wang, G.; Chen, Y.; Tasch, A.;
Electron Devices Meeting, 1998. IEDM '98 Technical Digest., International
6-9 Dec. 1998 Page(s):517 - 520
Digital Object Identifier: 10.1109/IEDM.1998.746411
AbstractPlus | Full Text: EDE(340 KB) IEEE CNF

15. Measurement and modelling of arsenic and boron diffusion in oxygen im
on-insulator (SOI) layers
Godfrey, D.J.; Chatter, R.; Robinson, A.K.; Augustus, P.D.; Alderman, J.R.; Da
J.; Hermenik, P.L.F.;
SOS/SOI Technology Workshop, 1988. Proceedings., 1988 IEEE
3-5 Oct. 1988 Page(s):42
Digital Object Identifier: 10.1109/SOI.1988.95416
AbstractPlus | Full Text: EDE(68 KB) IEEE CNF



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